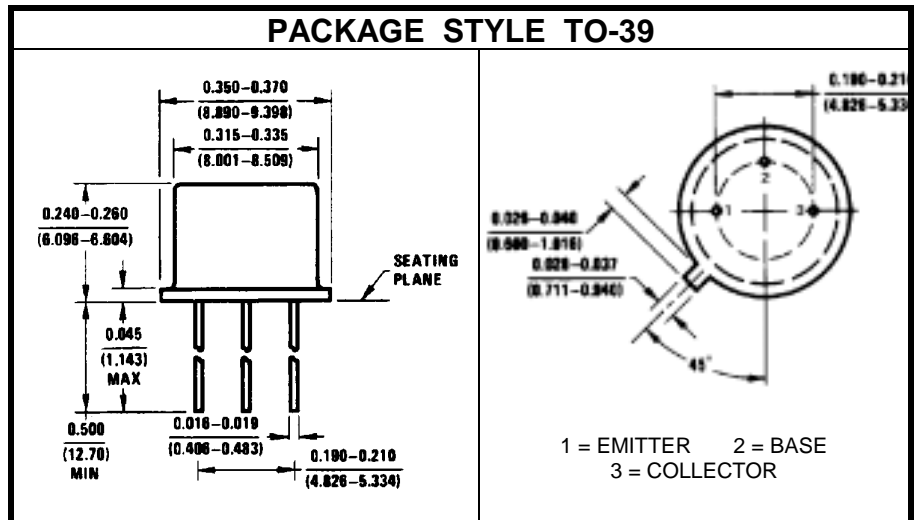


# SILICON NPN RF POWER TRANSISTOR

**DESCRIPTION:** The MRF237 is designed for large signal power amplifier applications operating to 225 MHz

## MAXIMUM RATINGS

|               |                                  |
|---------------|----------------------------------|
| $I_C$         | 1.0 A                            |
| $V_{CB0}$     | 36 V                             |
| $V_{CEO}$     | 18 V                             |
| $P_{DISS}$    | 8.0 W @ $T_C = 25^\circ\text{C}$ |
| $T_J$         | -65 °C to +200 °C                |
| $T_{STG}$     | -65 °C to +200 °C                |
| $\theta_{JC}$ | 22 °C/W                          |



## CHARACTERISTICS $T_C = 25^\circ\text{C}$

| SYMBOL     | TEST CONDITIONS  | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|------------|--|---------|---------|---------|-------|
| $BV_{CEO}$ | $I_C = 10\text{ mA}$   | 18      |         |         | V     |
| $BV_{CES}$ | $I_C = 5.0\text{ mA}$  | 36      |         |         | V     |
| $BV_{EBO}$ | $I_C = 1.0\text{ mA}$  | 4.0     |         |         | V     |
| $I_{CBO}$  | $V_{CE} = 15\text{ V}$   |         |         | .25     | mA    |
| $h_{FE}$   | $V_{CE} = 5.0\text{ V}$ $I_C = 250\text{ mA}$                          | 5.0     |         |         | ---   |
| $C_{OB}$   | $V_{CB} = 15\text{ V}$ $f = 1.0\text{ MHz}$                            |         | 15      | 20      | pF    |
| $G_{PE}$   | $V_{CC} = 12.5\text{ V}$ $P_{OUT} = 4.0\text{ W}$ $f = 175\text{ MHz}$ | 12      | 14      |         | dB    |
| $\eta$     |  | 50      | 62      |         | %     |

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